TRIACs, 16A

Snubberless, Logic Level and Standard

Features

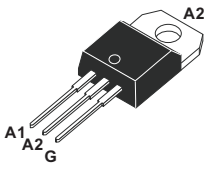
- Medium current Triac
- Low thermal resistance with clip bonding
- Low thermal resistance insulation ceramic for insulated 16T
- High commutation (4Q) or very high commutation (3Q) capability
- RoHS compliant, UL certified (File NO:E320098)
- Insulated tab (16TxxAI series, rated at 2500 V_{RMS})

Applications

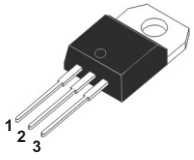
- Snubberless versions (With Suffix W) especially recommended for use on inductive loads, because of their high commutation performances
- On/off or phase angle function in applications such as static relays, light dimmers and appliance motor speed controllers

Description

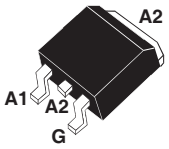
Available either in through-hole or surface-mount packages, the 16TxxA and 16TxxAI triacs series are suitable for general purpose mains power AC switcging



TO-220AB (**non-Insulated**)
(16TxxA)

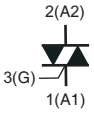


TO-220AB **(Insulated)**
(16TxxAI)



TO-263 (**D^2PAK)**
(16TxxH)

TO-220F **(ITO-220AB)**
(16TxxAF)



SYMBOL	VALUE	UNIT
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	600 to 1000	V
$I_{GT(Q1)}$	5 to 50	mA

Device summary

SYMBOL	PARAMETER	16TxxAI[1]	16TxxA
$I_{T(RMS)}$	On-state RMS current	16	16
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage	600/800/1000	600/800/1000
I_{GT}(Snubberless)	Triggering gate current	35/50	35/50
I_{GT}(Logic level)	Triggering gate current	10	10
I_{GT}(Standard)	Triggering gate current	25/50	25/50

Note 1: Insulated

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**VALUE**	**UNIT**
RMS on-state current (full sine wave)	$I_{T(RMS)}$	TO-220/TO-263	T_c = 100ºC	16	A
		TO-220insulate/TO-220F (ITO-220AB)	T_c = 86ºC		
Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	I_{TSM}	F =50 Hz	t = 20 ms	160	A
		F =60 Hz	t = 16.7 ms	168	
I^2t Value for fusing	I^2t	t_p = 10 ms		128	A^2s
Critical rate of rise of on-state current $I_G = 2xI_{GT}$, $t_r \leq 100ns$	dI/dt	F =100 Hz	T_j =125ºC	50	A/µs
Peak gate current	I_{GM}	T_p =20 µs	T_j =125ºC	4	A
Average gate power dissipation	$P_{G(AV)}$	T_j =125ºC		1	W
Storage temperature range	T_{stg}			- 40 to 150	ºC
Operating junction temperature range	T_j			- 40 to 125	

◎ ELECTRICAL CHARACTERISTICS (T_J= 25 ºC unless otherwise specified)

SNUBBERLESS and Logic level (3 quadrants)							
SYMBOL	**TEST CONDITIONS**	**QUADRANT**		**16Txxxx**			**Unit**
				SW	**CW**	**BW**	
I_{GT}(1)	V_D = 12 V, R_L = 33Ω	I - II - III	MAX.	10	35	50	mA
V_{GT}		I - II - III	MAX.	1.3			V
V_{GD}	$V_D = V_{DRM}$, R_L = 3.3KΩ, T_j = 125°C	I - II - III	MIN.	0.2			V
I_H(2)	I_T = 500 mA		MAX.	15	40	55	mA
I_L	$I_G = 1.2\ I_{GT}$	I - III	MAX.	25	50	70	mA
		II		30	60	80	
dV/dt(2)	V_D = 67% V_{DRM}, gate open, T_j = 125°C		MIN.	40	500	1000	V/µs
(dI/dt)c(2)	(dV/dt)c = 0.1 V/µs	T_j = 125°C	MIN.	8.5	-	-	A/ms
	(dV/dt)c = 10 V/µs	T_j = 125°C		3	-	-	
	Without snubber	T_j = 125°C		-	8.5	14	

Note 1: Minimum I_{GT} is guaranted at 5% of I_{GT} max.
Note 2: For both polarities of A2 referenced to A1.

◎ ELECTRICAL CHARACTERISTICS (T_J= 25 ºC unless otherwise specified)

Standard (4 quadrants)						
SYMBOL	**TEST CONDITIONS**	**QUADRANT**		**16Txxxx**		**UNIT**
				C	**B**	
I_{GT}(1)	V_D = 12 V, R_L = 33Ω	I - II - III	MAX.	25	50	mA
		IV		50	100	
V_{GT}		ALL		1.3		V
V_{GD}	$V_D = V_{DRM}$, R_L = 3.3KΩ, T_j = 125°C	ALL		0.2		V
I_H(2)	I_T = 500 mA		MAX.	25	50	mA
I_L	$I_G = 1.2\ I_{GT}$	I - III - IV	MAX.	40	60	mA
		II		80	120	
dV/d_t(2)	V_D = 67% V_{DRM}, gate open, T_j = 125°C		MIN.	200	400	V/µs
(dV/dt)c(2)	(dI/dt)c = 7 A/ms, T_j = 125°C		MIN.	5	10	V/µs

STATIC CHARACTERISTICS

SYMBOL	TEST CONDITIONS			VALUE	UNIT
V_{TM}(2)	I_{TM} = 22.5 A, t_P = 380 µs	T_j = 25°C	MAX.	1.55	V
V_{t0}(2)	Threshold voltage	T_j = 125°C	MAX.	0.85	V
R_d(2)	Dynamic resistance	T_j = 125°C	MAX.	25	mΩ
I_{DRM} I_{RRM}	V_D = V_{DRM} V_R = V_{RRM}	T_j = 25°C	MAX.	5	µA
		T_j = 125°C		1	mA

Note 1: Minimum I_{GT} is guaranted at 5% of I_{GT} max.

Note 2: For both polarities of A2 referenced to A1.

THERMAL RESISTANCE

SYMBOL			VALUE	UNIT
$R_{th(j-c)}$	Junction to case (AC)	TO-220AB, D²PAK	1.2	°C/W
		TO-220AB Insulated, TO-220F	2.1	
$R_{th(j-a)}$	Junction to ambient S(1)=1cm²	D²PAK	45	°C/W
		TO-220AB Insulated, TO-220AB, TO-220F	60	

Note 1: S=Copper surface under tab

PRODUCT SELECTOR

PART NUMBER	VOLTAGE (xx)			SENSITIVITY	TYPE	PACKAGE
	600 V	800 V	1000 V			
16TxxA-B/16TxxAI-B	V	V	V	50 mA	Standard	TO-220AB
16TxxA-BW/16TxxAI-BW	V	V	V	50 mA	Snubberless	
16TxxA-C/16TxxAI-C	V	V	V	25 mA	Standard	
16TxxA-CW/16TxxAI-CW	V	V	V	35 mA	Snubberless	
16TxxA-SW/16TxxAI-SW	V	V	V	10 mA	Logic level	
16TxxH-B	V	V	V	50 mA	Standard	D²PAK
16TxxH-C	V	V	V	25 mA	Standard	
16TxxH-SW	V	V	V	10 mA	Logic level	
16TxxH-CW	V	V	V	35 mA	Snubberless	
16TxxH-BW	V	V	V	50 mA	Snubberless	
16TxxAF-B	V	V	V	50 mA	Standard	TO-220F (ITO-220AB)
16TxxAF-C	V	V	V	25 mA	Standard	
16TxxAF-SW	V	V	V	10 mA	Logic level	
16TxxAF-CW	V	V	V	35 mA	Snubberless	
6TxxAF-BW	V	V	V	50 mA	Snubberless	

ORDERING INFORMATION

ORDERING TYPE	MARKING	PACKAGE	WEIGHT	BASE Q'TY	DELIVERY MODE
16TxxA-yy	16TxxA-yy	TO-220AB	2.0g	50	Tube
16TxxAI-yy	16TxxAI-yy	TO-220AB (insulated)	2.3g	50	Tube
16TxxAF-yy	16TxxAF-yy	TO-220F(ITO-220AB)	2.5g	50	Tube
16TxxH-yy	16TxxH-yy	TO-236(D²PAK)	2.0g	50	Tube

Note: xx = voltage, yy = sensitivity

ORDERING INFORMATION SCHEME

16 T 06 A - BW

Current

16 = 16A

Triac series

Voltage

06 = 600V
08 = 800V
10 = 1000V

Package type

A = TO-220AB (non-insulated)
AI = TO-220AB (insulated)
AF = TO-220F (ITO-220AB, insulated)
H = TO-263 (D^2PAK)

I_{GT} Sensitivity

B = 50mA Standard
C = 25mA Standard
SW = 10mA Logic Level
BW = 50mA Snubberless
CW = 35mA Snubberless

Fig.1 Maximum power dissipation versus on-state rms current (full cycle)

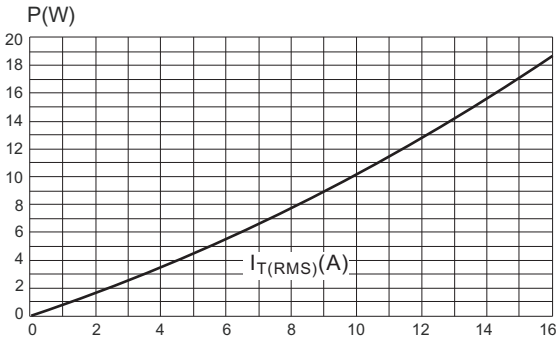


Fig.2 On-state rms current versus case temperature (full cycle)

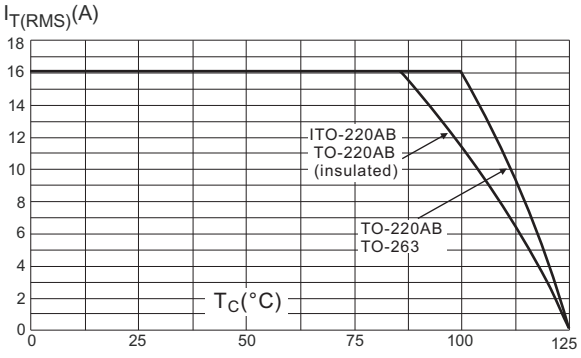


Fig.3 On-state current versus ambient temperature (full cycle)

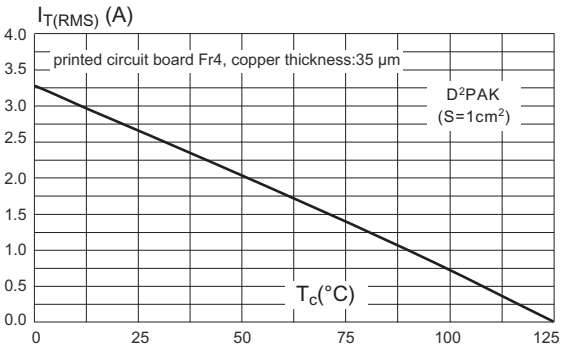


Fig.4 Relative variation of thermal impedance versus pulse duration

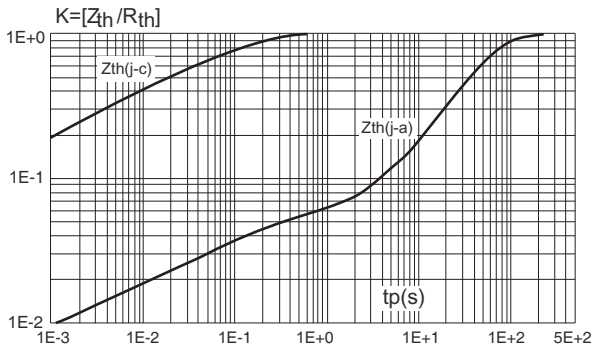


Fig.5 On-state characteristics (maximum values)

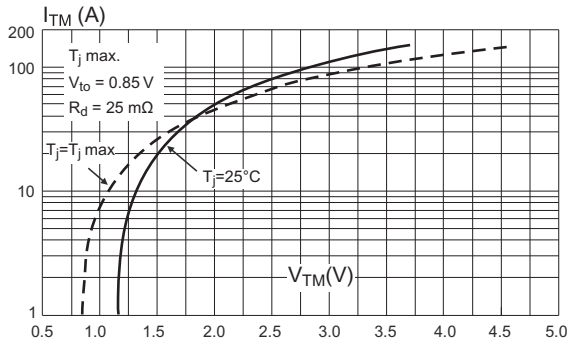


Fig.6 surge peak on- state current versus number of cycles

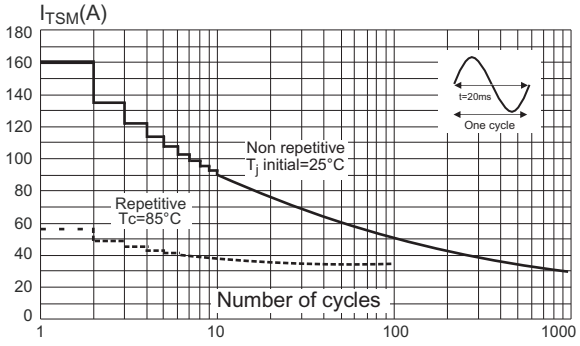


Fig7. Non-repetitive surge peak on-state current for a sinusoidal

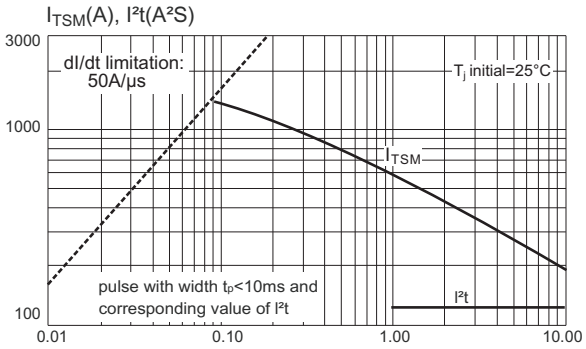


Fig.8 Relative variation of gate trigger current

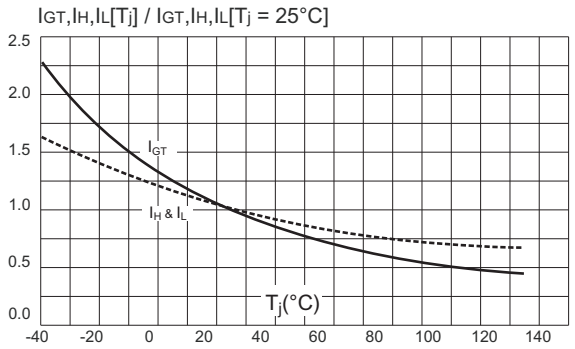


Fig.9 Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)

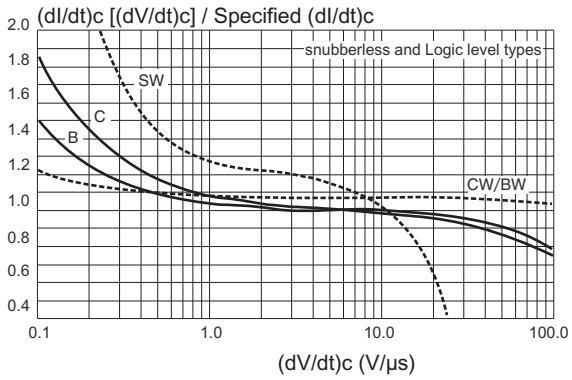


Fig.10 Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)

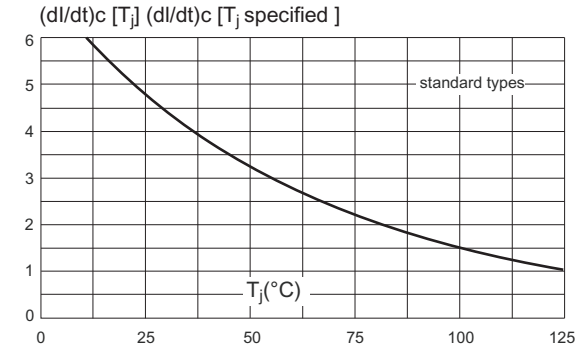
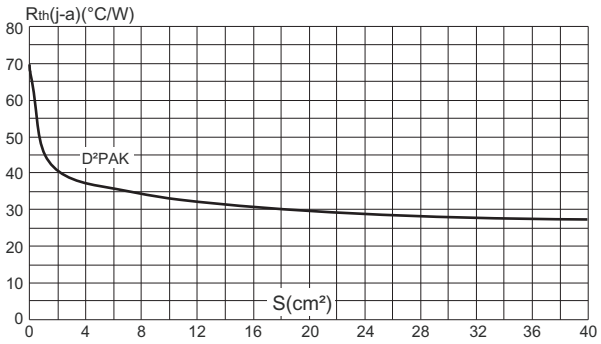
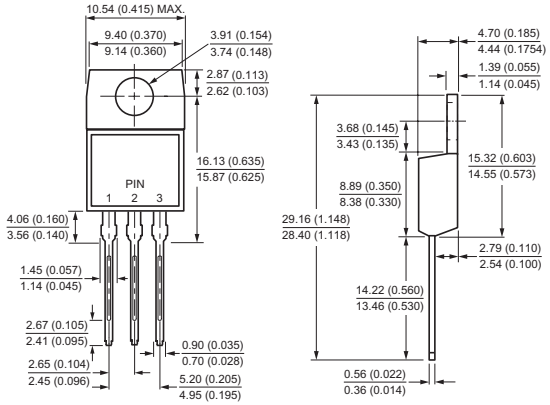


Fig.11 D²PAK thermal resistance junction to ambient versus copper surface under tab (printed circuit FR4, copper thickness: 35μm

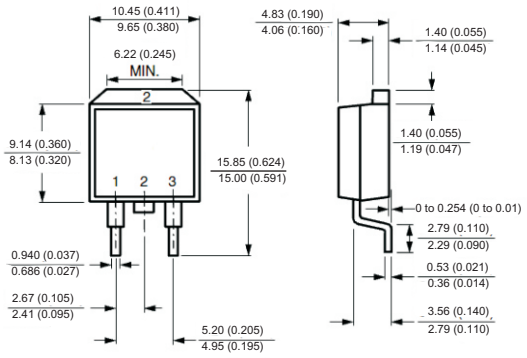


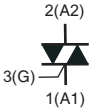
Case Style

TO-220AB



TO-263(D²PAK)

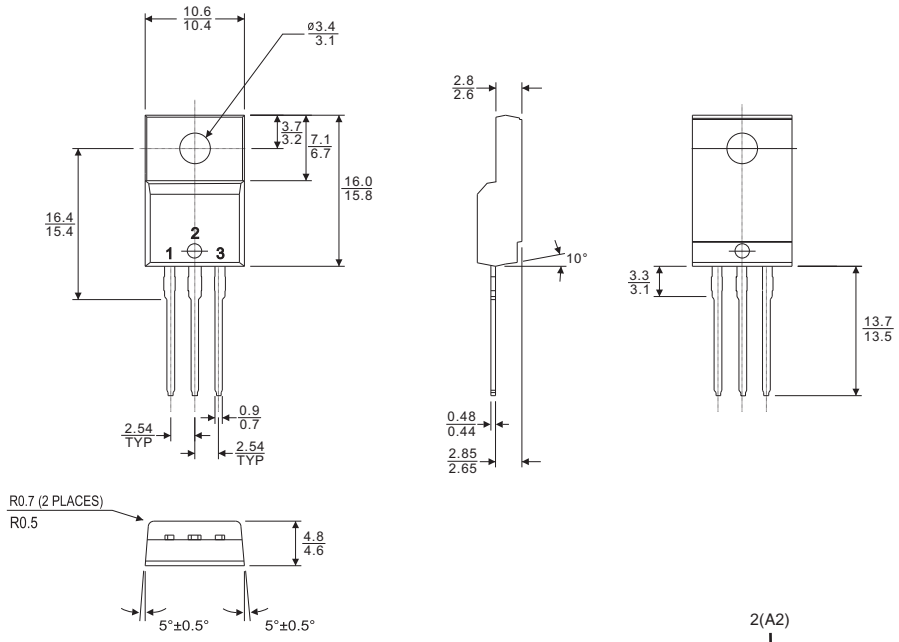




All dimensions in millimeters(inches)

Case Style

ITO-220AB



All dimensions in millimeters